

Stefan Wiefels

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8531780/publications.pdf>

Version: 2024-02-01

12
papers

447
citations

1040056

9
h-index

1474206

9
g-index

12
all docs

12
docs citations

12
times ranked

568
citing authors

#	ARTICLE	IF	CITATIONS
1	Reliability aspects of binary vector-matrix-multiplications using ReRAM devices. <i>Neuromorphic Computing and Engineering</i> , 2022, 2, 034001.	5.9	14
2	NEUROTEC I: Neuro-inspired Artificial Intelligence Technologies for the Electronics of the Future. , 2022, , .		0
3	Impact of the Ohmic Electrode on the Endurance of Oxide-Based Resistive Switching Memory. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 1024-1030.	3.0	26
4	Standards for the Characterization of Endurance in Resistive Switching Devices. <i>ACS Nano</i> , 2021, 15, 17214-17231.	14.6	128
5	Reliability Aspects of Memristive Devices for Computation-in-Memory Applications. , 2021, , .		0
6	A Consistent Model for Short-Term Instability and Long-Term Retention in Filamentary Oxide-Based Memristive Devices. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 58066-58075.	8.0	19
7	Intrinsic RESET Speed Limit of Valence Change Memories. <i>ACS Applied Electronic Materials</i> , 2021, 3, 5563-5572.	4.3	15
8	HRS Instability in Oxide-Based Bipolar Resistive Switching Cells. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 4208-4215.	3.0	32
9	Comprehensive model for the electronic transport in Pt/SrTiO_3 analog memristive devices. <i>Physical Review B</i> , 2020, 102, .	3.2	20
10	Statistical Modeling and Understanding of HRS Retention in 2.5 Mb HfO_2 based ReRAM. , 2020, , .		5
11	Processes and Effects of Oxygen and Moisture in Resistively Switching TaO_x and HfO_x . <i>Advanced Electronic Materials</i> , 2018, 4, 1700458.	5.1	85
12	Interfacial Metal-Oxide Interactions in Resistive Switching Memories. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 19287-19295.	8.0	103